



Express Mail No.: EL 451 599 045 US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Steven M. Chase, Connie J. Chang-Hasnain and Jeffrey M. Waite

Application No.: 09/693,612

Group Art Unit: 2872

Filed: October 20, 2000

Examiner: Ricky D. Shafer

For:

Apparatus and Method for

Attorney Docket No.: 9840-0053-999

Controlled Cantilever

Motion Through Torsional

Beams and a Counterweight

Date: December 6, 2002

SUPPLEMENTAL AMENDMENT AND RESPONSE TO OFFICE ACTION

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Enclosed are:

- an amendment responsive to the Office Action dated Nov. 5, 2002, for the above identified patent application; and
- a Petition for a One Month Extension of time to respond.

The Commissioner is hereby authorized to charge all fees that may be required, to Deposit Account No. 16-1150 (Order No. 9840-0053-999). A copy of this page is enclosed.

Respectfully submitted,

Date: December 6, 2002

31,066

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TECHNOLOGY CENTER 20

9840-0053-999, Amendment



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Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

This communication is responsive to the Office Action dated November 5, 2002, for the above identified patent application.

One Month Extension. Pursuant to 37 C.F.R. 1.136(a), the Applicant hereby petitions for a one-month extension of time to respond to the Office Action dated Nov. 5, 2002. This extension will extend the response due date to January 5, 2003.

In The Specification:

Rewrite the paragraph beginning at Page 14, Line 21, as follows:

The invention has been implemented with alternate wafer designs. The first design is a high-quality filter with DBR mirrors and narrow linewidth. The second is a simple three-layer structure with a large gap and low-finesse filtering characteristics. Figure 9 illustrates a high-finesse cavity, MBE-grown wafer that may be processed to form the structure of the invention. The designed center filter wavelength is 950 nm. The wafer was grown using Molecular Beam Epitaxy (MBE) using Be for p-doping and Si for n-doping. It is grown on

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